

Weak phase separation in electron-doped cuprates

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We study the quantum transition from an antiferromagnet to a superconductor in a model for electron- and hole-doped cuprates by means of a variational cluster perturbation theory approach. In both cases, our results suggest the occurrence of phase separation between a mixed antiferromagnetic-superconducting phase at low doping and a pure superconducting phase at higher doping. However, in the electron-doped case the energy scale for phase separation is an order of magnitude smaller than for hole doping. We argue that this can explain the different pseudogap and superconducting transition scales in hole- and electron-doped materials.

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High-temperature superconducting materials (HTSC) are characterized by strong electronic correlations which are responsible for a number of anomalous properties and competing phases. The occurrence of these anomalous phases is probably related to the close vicinity to the Mott-insulating and antiferromagnetic (AF) phases at half filling. This is particularly true for hole- (p-)doped materials which, besides the AF and the superconducting (SC) states, display a number of unconventional phases such as stripes [1, 2], checkerboard structures [3], non-Fermi liquid phases, etc. It has been argued that these inhomogeneous phases originate from the fact that in models with local interactions such as Hubbard or t - J the AF phase becomes unstable upon doping, possibly leading to phase separation [2]. On the other hand, long-range Coulomb repulsion enforces charge homogeneity at long distances so that stripes or other short-range inhomogeneous structures originate as a compromise between the two competing effects. It has been suggested that the high-temperature pseudogap at T^* observed in p-doped materials could be related to the onset of fluctuations of these inhomogeneous structures [2], so that one would expect the T^* energy scale to be related to the phase-separation scale.

The situation seems quite different in electron- (n-)doped cuprates. Here, a direct transition seems to occur from AF to SC [4] suggesting a quantum-critical point (QCP) and no phase separation [5]. This is supported by the fact that inhomogeneous structures have not been observed in n-doped materials so far. On the other hand, a high-energy pseudogap has been observed in n-doped cuprates as a suppression of angle-resolved photoemission spectrum (ARPES) spectral weight near the Fermi surface (FS) crossing of the magnetic Brillouin Zone [6]. Recently, in two n-doped compounds also a low-energy pseudogap has been detected under the SC transition temperature [7], i.e., at much lower temperatures than in p-doped compounds. The question arises whether the striking differences between the phase diagram of n- and p-doped cuprates, namely the fact that the AF phase extends to higher doping [8], while the SC phase takes a more restricted doping range, are only quantitative or there are also more fundamental differences, i.e., a different evolution from the AF to the SC phase.

In this paper, we address the question of the AF to

SC transition by an analysis of the single-band Hubbard model for parameters appropriate to n- and p-doped compounds via variational cluster perturbation theory (VCPT) [9, 10]. VCPT is appropriate to deal with strongly-correlated systems, since the short-range interaction part is solved exactly within a small cluster. A similar analysis has been recently carried out by Senechal et al. [11]. Our results show (see below) that the issue of phase separation for the AF to SC transition in n-doped materials requires a high accuracy in the determination of energies, which was possible within the present work only thanks to two technical improvements of the VCPT calculations, which we are going to describe in detail below. As in Ref. 11, we find that the AF phase mixes with a weak d-wave SC component at small doping. A similar coexistence phase has been also obtained by Lichtenstein and Katsnelson [12] by a cluster dynamical mean-field calculation, as well as in earlier mean-field calculations [13]. At higher doping there is a transition to a pure d-wave SC phase.

Our main results (see Fig. 1) are the following: in p-doped systems the situation is quite clear: the transition is first order in x , i.e., there is an instability towards phase separation with a jump in doping x . We stress that by allowing for a more general space dependence of the order parameter, this macroscopic phase separation could be possibly replaced by other microscopically inhomogeneous phase, such as, e.g., stripes. Certainly, this is expected to be the case if long-range Coulomb interaction is taken into account [2]. Our calculation (see blow up in Fig. 1) suggests phase separation also in the n-doped case, although the corresponding energy scale is one order of magnitude smaller than in p-doped compounds.

We consider the two-dimensional single-band Hubbard model with nearest-neighbor (t) and next-nearest-neighbor (t^0) hoppings, and Hubbard repulsion U . We take typical parameters valid for both hole- and electron-doped high- T_c cuprates [14], namely $t^0/t = 0.3$ and $U/t = 8$. The aim of our calculation is a qualitative and semiquantitative description of the materials so that we don't carry out an accurate fitting of the parameters. We have checked that different values for the parameters (e.g., a different U) or a third-neighbor hopping does not change our results qualitatively.

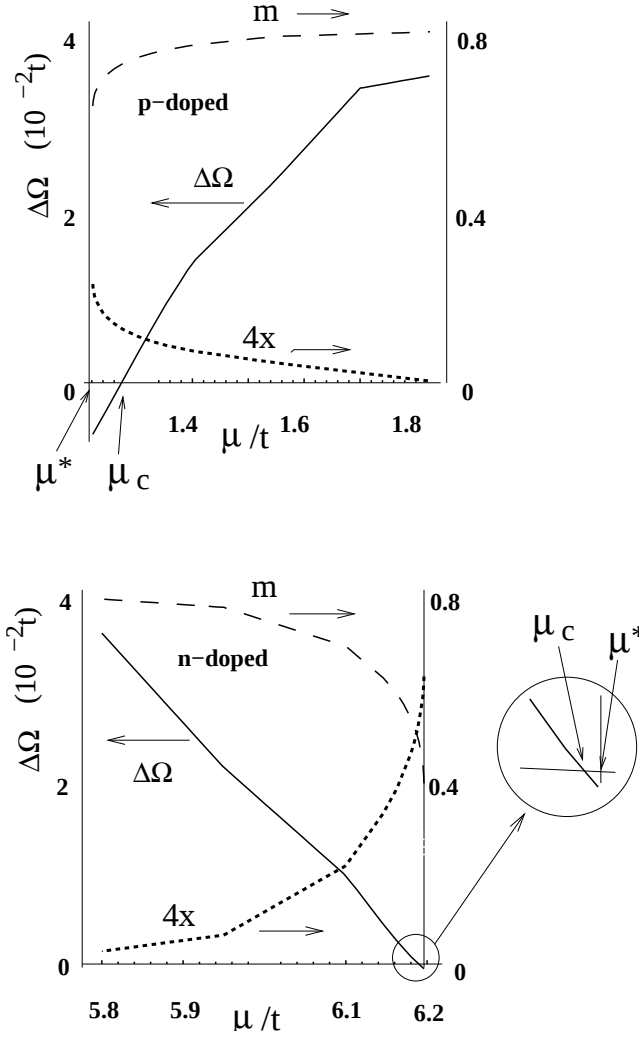


FIG. 1: Difference between the $T = 0$ grand-canonical potentials $\Omega_{SC} - \Omega_{AF+SC}$ of the SC and the AF+SC phase (solid line), staggered magnetization m (dashed), doping x (dotted, scaled by a factor 4 for convenience) in the AF+SC phase plotted as a function of chemical potential μ/t for the Hubbard model with $U = 8t$ and $t^0/t = 0.3$ for hole and electron doping. Right: blowup of the region around the transition for the n-doped case: Here, $\mu_c = 6.189$, and $\mu^* = 6.196$.

Within the CPT approach [15, 16], the lattice is partitioned into disconnected clusters. The Hamiltonian H_{CPT}^0 of the disconnected lattice can be solved by exact diagonalization. The intercluster hopping Hamiltonian V_{CPT} is then treated perturbatively up to first order for the self-energy. VCPT (or SFA) [10, 17] generalizes this approach by decomposing H into a "reference" part H^0 and a "perturbation" V , the latter containing single-particle terms only. In general, one can take $H^0 = H_{CPT}^0 + H$, where H is an arbitrary single-particle Hamiltonian. In order to conserve the total physical Hamiltonian $H = H_{CPT}^0 + V_{CPT}$, H must then be subtracted from V [17], which becomes $V = V_{CPT} - H$. This extension allows for the description of symmetry-broken phases by introducing, via H , a corresponding field. Notice that this field is only fictitious, since it is subtracted again via V . However, due to the fact that

the subtraction is only performed in a perturbative way, results in fact depend on H , except for the case where CPT becomes exact, i.e., for $U = 0$. This apparent "arbitrariness" in the choice of H is restricted by the requirement that the so-called self-energy functional [10] (which corresponds to the CPT grand-canonical potential)

$$\Omega = \Omega^0 + \text{Tr} \ln(G_{CPT}) - \text{Tr} \ln(G^0) \quad (1)$$

has to be stationary with respect to H . In (1), Ω^0 and G^0 are the grand-canonical potential and the Green's function of the reference system (i.e. the cluster) H^0 , respectively, and G_{CPT} is the Green's function of the physical system H calculated perturbatively in V [17]. Physically, one can think VCPT as an extension of CPT in which the intercluster perturbation is not carried out with respect to the exact cluster ground state but with respect to an "optimized" state parameterized by H . This is similar in spirit to diagrammatic expansions in which the "bare" Green's functions are replaced by "dressed" mean-field Green's functions in some symmetry-broken state such as AF or SC.

Since we expect to describe both an AF and a d-wave SC phase, in our calculation, $H = H_{AF} + H_{SC} + H_{d-wave}$ contains both a staggered (h) and a nearest-neighbor d-wave pairing field (Δ), where

$$H_{AF} = h \sum_R (n_{R,\uparrow} - n_{R,\downarrow}) e^{iQ \cdot R} \quad (2)$$

$$H_{SC} = \frac{\Delta}{2} \sum_{R,R^0} (c_{R,\uparrow} - c_{R,\downarrow}) (c_{R^0,\uparrow} + c_{R^0,\downarrow}) \quad (3)$$

where $c_{R,\sigma}$ destroys an electron on lattice site R with spin projection σ , $n_{R,\sigma} = c_{R,\sigma}^\dagger c_{R,\sigma}$ is the corresponding density operator, $Q = (\pi, \pi)$ is the antiferromagnetic wave vector, and the d-wave factor $(R - R^0)$ is non-vanishing for nearest-neighbor lattice sites only and is equal to ± 1 (± 1) for $R - R^0$ in x (y) direction. In the SC term, the sum is restricted to R and R^0 belonging to the same cluster.

In addition to the symmetry-breaking terms, away from half filling it is necessary to add to the reference system a "fictitious" on-site energy

$$H_{on-site} = \epsilon \sum_R n_{R,\sigma} \quad (4)$$

which plays the role of a "shift" in the cluster chemical potential with respect to the "physical" chemical potential. Without this term, which has been omitted in Ref. 11, the mean particle density $n = 1 - x$ (x is the doping, corresponds to p- and n-doping, respectively) cannot be unambiguously determined, as different results would be obtained by evaluating it as $n = \langle n \rangle$ or as the usual trace over the Green's function. Of course, a consistent treatment of the particle density is important for an accurate analysis of phase transitions as a function of doping. Unfortunately, the inclusion of ϵ considerably complicates the calculation, as now ϵ is not simply a minimum with respect to its parameters, but a saddle point

(typically a maximum in the ϵ direction). Physically, one can regard λ as a Lagrange multiplier which enforces an appropriate constraint in the particle number [18]. A long this constraint, λ is then a minimum with respect to h and ϵ .

For a proper characterization of the phase transition it is necessary to evaluate ϵ with high accuracy. This is difficult to achieve by simply numerically carrying out the frequency integrals contained in the trace in (1). It is rather convenient to exploit the fact that these integrals can be replaced (at zero temperature T) by a sum over the negative poles of $G_{\text{CPT}}(q)$ and of G^0 (see Ref. 19 for details). While the latter are directly given by the single-particle and single-hole excitation energies of the cluster, the former can be directly obtained as the eigenvalues of the matrix $h_{\alpha\beta}$ in Eq. (17) of Ref. 20 [18]. Since this method requires the evaluation of all cluster single-particle and single-hole states, a complete diagonalization of the cluster Hamiltonian must be carried out. In addition, the dimension of the matrix $h_{\alpha\beta}$ is equal to the number of single-particle and single-hole states. This severely restricts the maximum cluster sizes that can be considered in our VCPT calculation. For this reason, we only consider a 2×2 cluster as a reference system.

Our calculation, thus, proceeds as follows. For a given value of the variational parameters ϵ , h , and λ we carry out a complete diagonalization of the cluster Hamiltonian (due to the presence of the pairing field, particle number is not conserved), evaluate ϵ as described above and look for a stationary solution as a function of the variational parameters. Quite generally, different stationary solutions can be found, corresponding, for example, to different phases. In this case, the minimum ϵ selects the most stable one. Near half filling the two most stable solutions are a coherently mixed AF+SC and a pure SC phase. Results for these solution are plotted in Fig. 1 for the p- and n-doped cases. The AF order parameter m is plotted as a dashed line for both n- and p-doped systems as a function of ϵ . m monotonously decreases upon decreasing ϵ (for p-doping) or increasing ϵ (for n-doping) away from half filling. In Fig. 1 we also plot the doping x and the difference between the $T = 0$ grand-canonical potentials $\epsilon_{\text{SC}} - \epsilon_{\text{AF+SC}}$ of the two most stable solutions, namely the SC and the AF+SC one. While at lower doping, the AF+SC phase is the most stable one, a level crossing occurs at a critical chemical potential ϵ_c for which m is still nonzero, i.e. the transition is first order as a function of ϵ both for the p- as well as for the n-doped case. Although from Fig. 1 this effect seems tiny for the n-doped case, we stress that our calculation has been done with sufficient accuracy to resolve this difference. At this value of ϵ , the doping x_c of the AF+SC solution is different from the one x_c^0 of the pure SC phase so that there is a jump $x = x_c^0 - x_c > 0$ in the doping at ϵ_c indicating phase separation between a weakly doped AF+SC and a higher doped SC phase. For some $\epsilon = \epsilon_c$ (further away from half filling than ϵ_c) the AF+SC solution ceases to exist. In principle, an unstable AF+SC solution continues to exist for $x > x_c$. Here ϵ is a decreasing function of the particle density, an equivalent

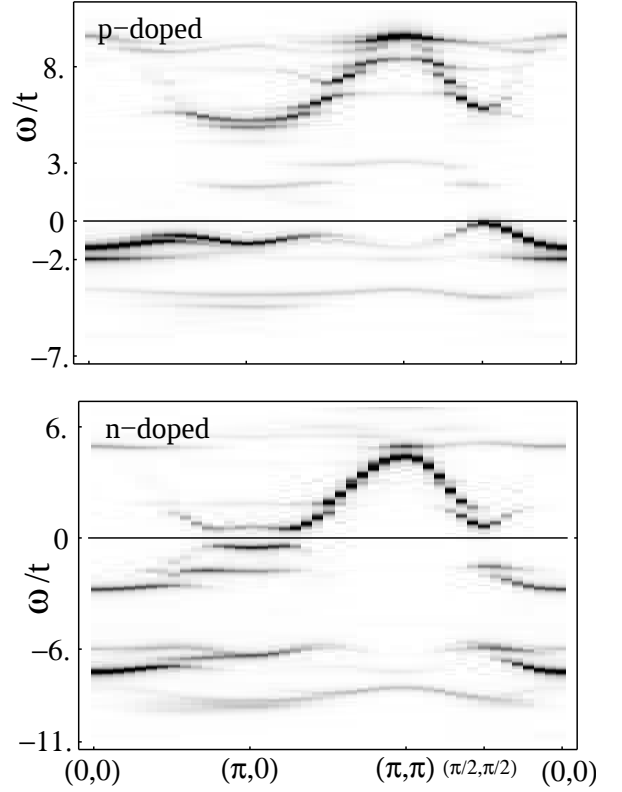


FIG. 2: Single-particle spectrum for the hole-doped (a) and for the electron-doped system (b) close to the AF+SC to SC transition, i.e., for dopings $x = 0.03$ and $x = 0.13$, respectively.

indication of phase separation.

The difference $\epsilon_j - \epsilon_{\text{AF+SC}}$ can be seen as a measure of the characteristic phase-separation energy, i.e., it is proportional to the energy barrier between the two doping values. As one can see from Fig. 1, in the p-doped case this energy scale ($\approx t \cdot 5 \cdot 10^{-2}$) is about an order of magnitude larger than in the n-doped solution ($\approx t \cdot 7 \cdot 10^{-3}$). Taking typical values for the energy measure t ($t \approx 0.25\text{eV}$), this corresponds to a temperature scale of 125K in p-doped, and 18K in electron-doped cuprates, which is of the order of the corresponding pseudogap temperature scales. Also the discontinuity Δx (not shown) is larger in the p-doped case ($\Delta x = 0.11$, vs. $\Delta x = 0.08$ for n-doped), although the difference is not significant. At the same time, the doping at which the AF+SC solution is destroyed is much larger in n-doped ($x_c = 0.13\%$) than in p-doped systems ($x_c = 0.03\%$), in qualitative agreement with experiments [4, 8]. Therefore, our results suggest that the AF+SC to SC transition as a function of ϵ is clearly first order in the p-doped case while weakly first order (almost second order) for n-doping.

The different behavior between the two kinds of systems can be understood by looking at the doping evolution of the single-particle spectrum from the AF insulator to a SC displayed in Fig. 2. In agreement with experiments [6, 21], in p-doped cuprates doped holes first enter at $(\pi, 2\pi)$ [22]. On the other hand, in n-doped materials doped electrons initially form pockets around

(π ; 0) [5, 6, 21]. At (π ; 0) the density of states is larger and the fact that ϵ_F lies within the SC gap apparently stabilizes the AF solution for a larger doping range, allowing for the AF gap to decrease more gradually in the n-doped case. The transition to a non magnetic solution appears to occur as soon as the Fermi energy touches the top of the band at (π ; ± 2). At this nodal point the SC gap is zero, so that doping into nodal particles apparently destabilizes the AF solution. This appears to be the reason why in the p-doped case the AF solution, where hole are first doped near (π ; ± 2) (see also Ref. 5), is stable only in a smaller doping range. Numerically, we observe the following behavior: as long as ϵ_F remains below (above for p-doped) the band around (π ; ± 2), there is only an absolute minimum of ϵ_F at a finite value h_{opt} of the staggered field h (we keep the other two fields h_x and h_y at their saddle point). As soon as ϵ_F enters the band at (π ; ± 2), h_{opt} also develops a local minimum at $h = 0$, which becomes rapidly smaller than the minimum $h = h_{\text{opt}}$. Eventually, the maximum between the two minima at $h = 0$ and $h = h_{\text{opt}}$ merges into the minimum at $h = h_{\text{opt}}$ so that this latter saddle point disappears. The observation that doping into (π ; ± 2) makes the AF phase unstable suggests that the occurrence of phase separation is generic and quite independent on specific parameters (unless, of course, one adds some doping-dependent potential). Finally, let us mention that the Fermi-surface evolution of the n-doped system as a function of x (not shown) qualitatively reproduces the ARPES experiments [6]: For small doping we obtain electron pockets around (π ; 0), while for larger doping we obtain an evolution to a large Fermi surface centered around (π ; π).

The VCPT method exactly treats fluctuations up to the range of the cluster size, so that the question arises whether the SC solution we (and also others [11, 12]) obtain within the AF phase is a true long-range SC phase or whether it is only a signal of strong pairing fluctuations within the AF phase. The latter hypothesis is supported by the fact that results obtained with different cluster sizes [11] seem to indicate a strong size dependence of the SC order parameter. In this case, certainly our results implies that the SC pseudogap associated with these pairing fluctuations is important in order to stabilize the AF phase in n-doped materials. In fact, a more detailed analysis shows that the field h does not only play the role of a "self consistent" pairing field, but it also contributes to the screening of the Hubbard interaction U by increasing charge fluctuations and, accordingly, to the transfer of spectral weight from the upper Hubbard band (which in our calculation – contrary to Hartree-Fock – is different from the upper AF band) to just above the Fermi level. h is, for instance, responsible for the band at ϵ_F also observed in Ref. 11. On the other hand, h hardly has an effect in p-doped systems since it does not produce any gap, as doping occurs near the nodal points first.

In conclusion, our calculations suggest that the AF to

SC transition in n-doped systems is associated with a tendency towards phase separation, similarly to p-doped materials, although with an energy scale which is one order of magnitude smaller. In the presence of Coulomb interaction, this tendency is expected to produce a microscopically segregated phase, such as stripes or similar structures [23]. Following the idea that the pseudogap temperature is related to the formation of such segregated phases [2], our results are consistent with the fact that the pseudogap temperature is much smaller in n-doped than in p-doped cuprates.

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